

IGBT Modules

IGBT Module (X series) 650V / 50A / IPM

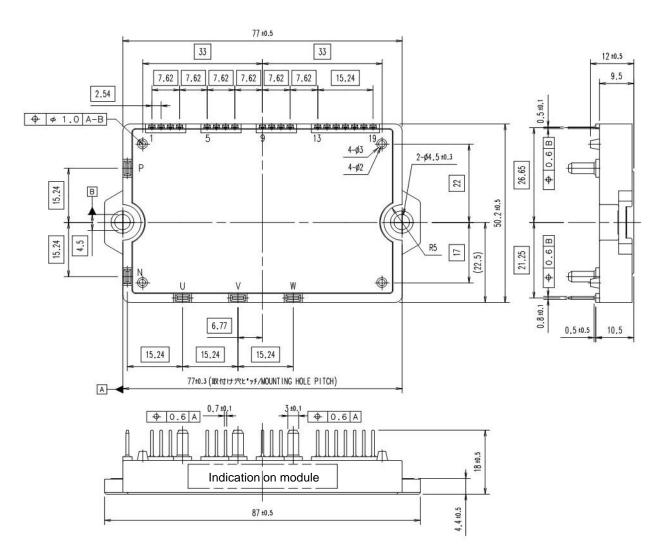
Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- ·Low power loss and soft switching
- · High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of

parts in built-in control circuit



■ Outline drawing (Unit : mm)



Weight:100g(typ.)



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Absolute maximum ratings

 $T_{\rm C}$ =25°C, $T_{\rm vi}$ =25°C, $V_{\rm CC}$ =15V unless otherwise specified

	Item	Symbol	Conditions	Min.	Max.	Units
Сс	llector-emitter voltage	V _{CES}	*1	-	650	V
Sh	ort circuit voltage	V _{SC}	*2	200	400	V
Ľ		/ _C	DC	-	50	А
Inverter	Collector current	/ _{CP}	1ms	-	100	Α
λθ		-/ _C	Duty=100% *3	-	50	Α
-	Total power dissipation	P _{tot}	IGBT 1 device *4	-	217	W
	Collector current	/ _C	DC	-	-	Α
ke		I _{CP}	1ms	-	-	Α
Brake	Forward current of diode	/ _F		-	-	Α
	Total power dissipation	P _{tot}	IGBT 1 device *4	-	-	W
Su	pply voltage of pre-driver	V _{CC}	*5	-0.5	20	V
Inp	out signal voltage	V _{in}	*6	-0.5	$V_{\rm CC} + 0.5$	V
Ala	arm signal voltage	V _{ALM}	*7	-0.5	V _{CC}	V
Ala	arm signal current	/ _{ALM}	*8	-	20	mΑ
Tv	_j Warning signal voltage	V _{WNG}	*9	-0.5	V _{CC}	V
Tv	j Warning signal current	I _{WNG}	*10	-	20	mA
Vir	tual junction temperature	Τ _{vj}		-	175	°C
Op	perating virtual junction temperature	T _{vjop}		-	150	°C
Op	perating case temperature	T _c		-20	125	°C
Sto	orage temperature	T _{stg}		-40	125	°C
So	Ider temperature	T _{sol}	*11	-	260	°C
lsc	plating voltage	V _{isol}	*12	-	2500	Vrms
Mo	ounting torque of screws to heat sink	Ms	Mounting(M4)	-	1.7	Nm
Мс	ounting torque of screws to terminals	M _t	Main terminals(M4)	-	-	Nm

Notes

*1: V_{CES} shall be applied to the input voltage between terminal P-(U,V, W) and (U,V, W)-N.

*2: In the case of the load inductance to be over 1μ H.

*3: Duty=150°C/ $R_{th(j-c)D}/(I_F \times V_F Max.) \times 100$

*4: P_{tot}=150°C/R_{th(j-c)Q}

*5: V_{CC} shall be applied to the input voltage between terminal No.4 and 1, 8 and 5, 12 and 9, 14 and 13.

*6: V_{in} shall be applied to the input voltage between terminal No.3 and 1, 7 and 5, 11 and 9, 16~18 and 13.

*7: V_{ALM} shall be applied to the voltage between terminal No.2 and 1, 6 and 5, 10 and 9, 19 and 13.

*8: /_{ALM} shall be applied to the input current to terminal No.2,6,10 and 19.

*9: V_{WNG} shall be applied to the voltage between terminal No.15 and 13.

*10: I_{WNG} shall be applied to the input current to terminal No.15.

*11: Immersion time 10±1sec. 1 time.

*12: Terminal to base, 50/60Hz sine wave 1 min. All terminals should be connected together during the test.

Electrical characteristics

Main circuit

 T_{vi} =25°C, V_{CC} =15V unless otherwise specified

	İtem	Symbol	Co	nditions	Min.	Тур.	Max.	Units
er	Collector current at off signal input	I _{CES}	V _{CE} =650V		-	-	1.0	mA
Inverter	Collector-emitter	$V_{\text{CE(sat)}}$	1 _c =50A	Terminal	-	-	1.60	V
Ž	saturation voltage	 CE(sat) 		Chip	-	1.15	-	V
<u> </u>	Forward voltage of FWD	V _F	/ _F =50A	Terminal	-	-	2.00	V
	I of ward voltage of 1 WD	¥ F		Chip	-	1.50	-	V
0	Collector current at off signal input	I _{CES}			-	-	-	mA
Brake	Collector-emitter	$V_{CE(sat)}$		Terminal	-	-	-	V
	saturation voltage	V CE(sat)		Chip	-	-	-	V
	Forward voltage of FWD	V _F		Terminal	•	-	•	V
	Torward voltage of T VD	ΥF		Chip	-	-	-	V
Switc	hing time	t _{on}	1 _c =50A	T _{vi} =150°C	0.5	-	-	μs
*13		t _{d(on)}	$V_{\rm DC} = 300 V$		0.5	-		μs
		$t_{\rm off}$			-	-	2.0	μs
		$t_{d(off)}$			-	-	1.7	μs
		t _{rr}	I _F = 50A	T _{vi} =150°C	-	-	0.5	μs
		۰rr	$V_{\rm DC}$ = 300V					

*13: Turn on time $(t_{on}) = t_{d(on)} + t_r$, Turn off time $(t_{off}) = t_{d(off)} + t_f$



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Control circuit

 T_{vj} =25°C, V_{CC} =15V unless otherwise specified

Item	Symbol	Conditions		Min.	Тур.	Max.	Units
Supply current of P-side pre-driver (per one unit)	/ _{ccp}	Switching frequency $(f_{SW}) = 0^{-1}$ $T_{C} = -20 \sim 125^{\circ}C$	~15kHz	-	-	11	mA
Supply current of N-side pre-driver	/ _{ccn}			-	-	27	mA
Input signal threshold voltage	$V_{inth(on)}$	V _{in} -GND	ON	1.2	1.4	1.6	V
input signal threshold voltage	$V_{\text{inth(off)}}$	V in OND	OFF	1.5	1.7	1.9	V

Protection circuit

 T_{vi} =25°C, V_{CC} =15V unless otherwise specified

lter	n	Symbol	Conditions	Min.	Тур.	Max.	Units
Over current	Inverter	I _{oc}	T _{vj} =150°C	75	-	-	Α
protection level	Brake	100		-	-	-	Α
Over current protection	n delay time	t _{dOC}	T _{vj} =150°C	-	4.0	-	μs
Short circuit protection	n delay time	t _{dSC}	T _{vj} =150°C	-	1.0	-	μs
IGBT chips over heati protection temperatur		Т _{јОН}	Surface of IGBT chips	175	-	-	°C
Over heating protection	on hysteresis	T _{jH}		-	20	-	°C
IGBT chips warning te	emperature level	T _{jW}	Surface of IGBT chips (Y)	150	-	-	
Warning hysteresis		T _{jWH}		-	10	-	
Under voltage protect	ion level	V _{UV}		11.0	-	12.5	V
Under voltage protect	ion hysteresis	V _H		0.2	0.5	-	V
		t _{ALM(OC)}	ALM-GND	1.0	2.0	2.4	ms
Alarm signal hold time	9	$t_{ALM(UV)}$	$T_{\rm C}$ =-20~125°C $V_{\rm cc} \ge 10V$	3.5	4.0	4.5	ms
		t _{ALM(TjOH)}		7.0	8.0	9.0	ms
Warning signal hold ti	me	t _{WNG}	WNG-GND	T _{jw} c	operati	ng ~	ms
Warning eignarhold t		WING	T _C =-20∼125°C	ca	ncella	tion	
Alarm signal voltage		V _{ALMH}	ALM-GND, without protection	14.5	-	15.0	V
Warning signal voltag	е	V_{WNGH}	WNG-GND, without warning	14.5	-	15.0	V
Resistance for curren	t limit	R_{ALM}		960	-	1570	Ω
	t mint	R _{WNG}		960	-	1570	Ω

■ Thermal resistance characteristics (*T*_c = 25°C)

ltem		Symbol	Min.	Тур.	Max.	Units	
Thermal resistance	Inverter	IGBT	$R_{\rm th(i-c)Q}$	-	-	0.69	K/W
iunction to case	Inverter	FWD	R _{th(i-c)D}	-	-	0.87	K/W
,	Brake	IGBT	$R_{\rm th(i-c)Q}$	-	-	-	K/W
*14	DIAKE	FWD	$R_{\rm th(i-c)D}$	-	-	-	K/W
Thermal resistance case to heat sink *15			$R_{\rm th(c-s)}$	-	0.05	-	K/W

I nermal resistance case to neat sink ~15

*14: For 1 device , the measurement point of the case is just under the chip.

*15: This is the value which is defined mounting on the additional heat sink with 1 W/(m K) thermal grease.

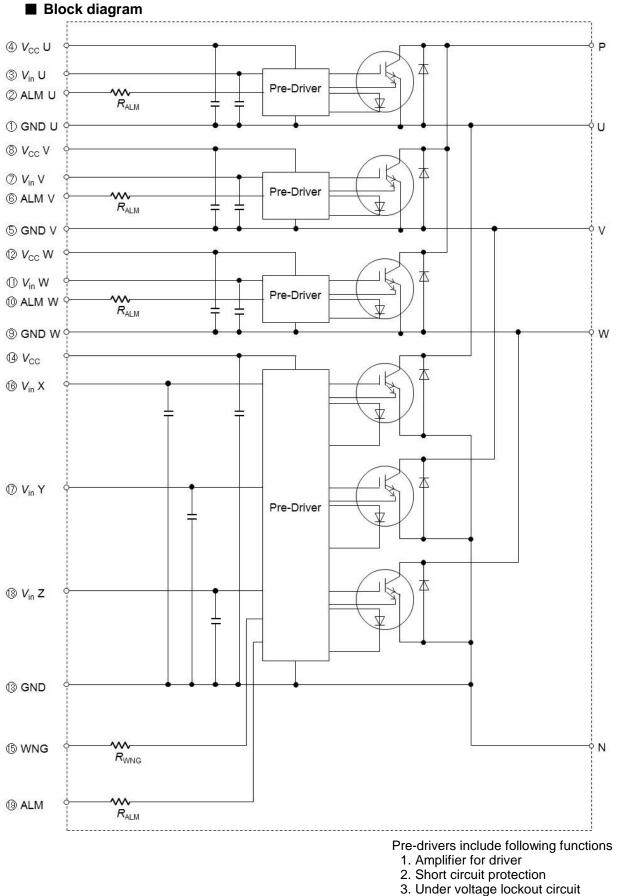
Noise immunity (V_{DC} =600V, V_{CC} =15V)

Item	Conditions	Min.	Тур.	Max.	Units
Common mode	Pulse width 1µs,polarity ±,10min.	+20			kV
rectangular noise	Judge: no over-current, no miss operating	±2.0	-	-	κv

Recommended operating conditions

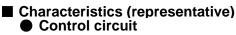
Symbol	Min.	Тур.	Max.	Units
V _{DC}	-	-	400	V
V _{cc}	13.5	15.0	16.5	V
f _{sw}	-	-	20.0	kHz
t_{dead}	1.5	-	-	μs
-	1.3	-	1.7	Nm
	V_{DC} V_{CC} f_{SW} t_{dead}	$\begin{array}{c c} V_{\text{DC}} & - \\ V_{\text{CC}} & 13.5 \\ f_{\text{SW}} & - \\ t_{\text{dead}} & 1.5 \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

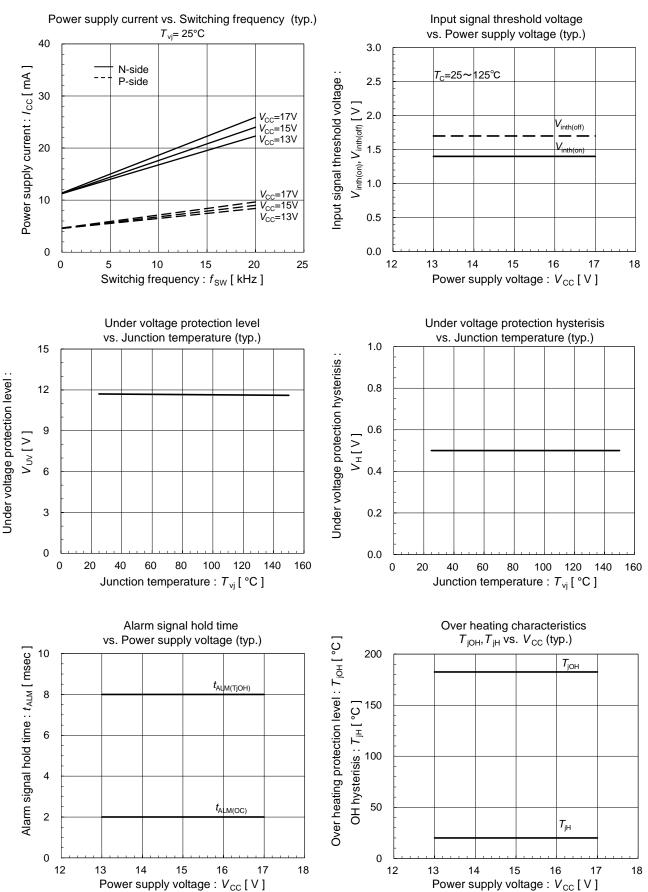




- 4. Over current protection
- 5. IGBT chip over heating protection

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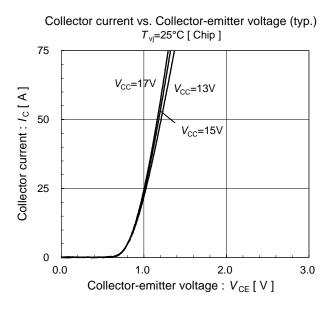




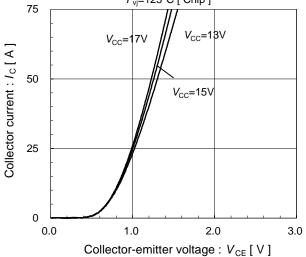


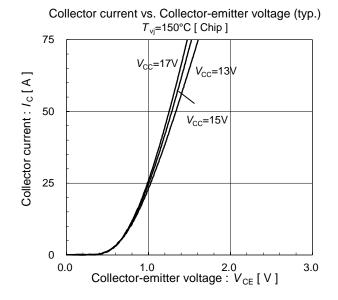
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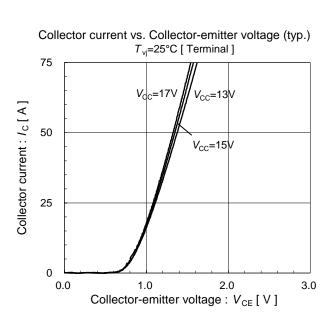
Inverter





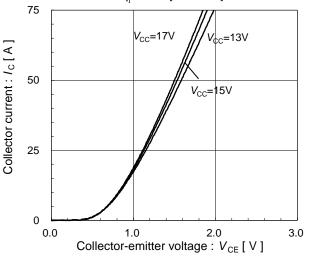






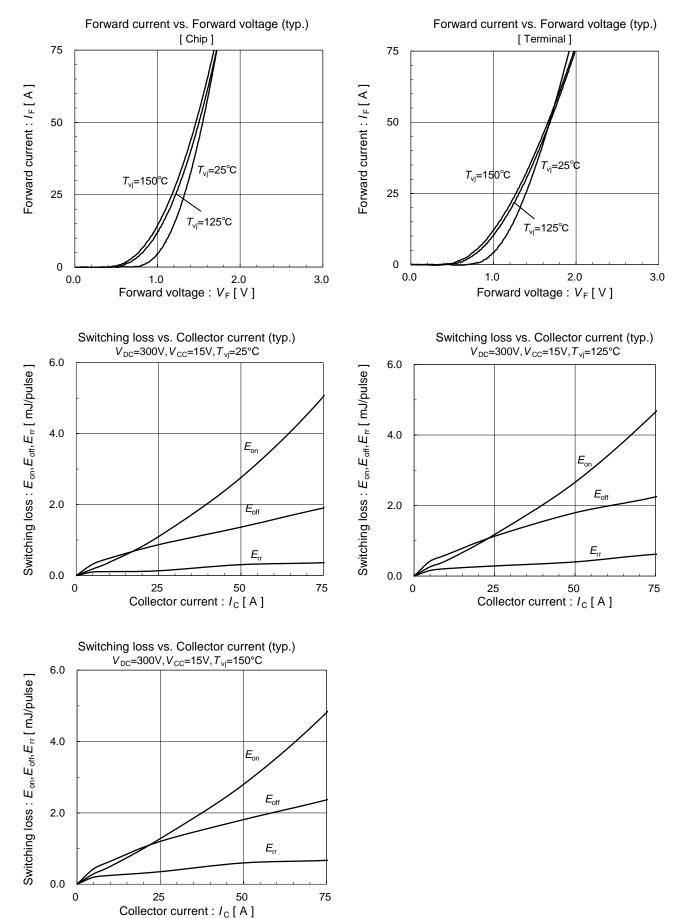
Collector current vs. Collector-emitter voltage (typ.) $T_{vj}=125^{\circ}C [Terminal]$ $T_{v_{c}c}=13V$ $V_{cc}=15V$ V_{cc}=15V$

Collector current vs. Collector-emitter voltage (typ.) T_{vi} =150°C [Terminal]



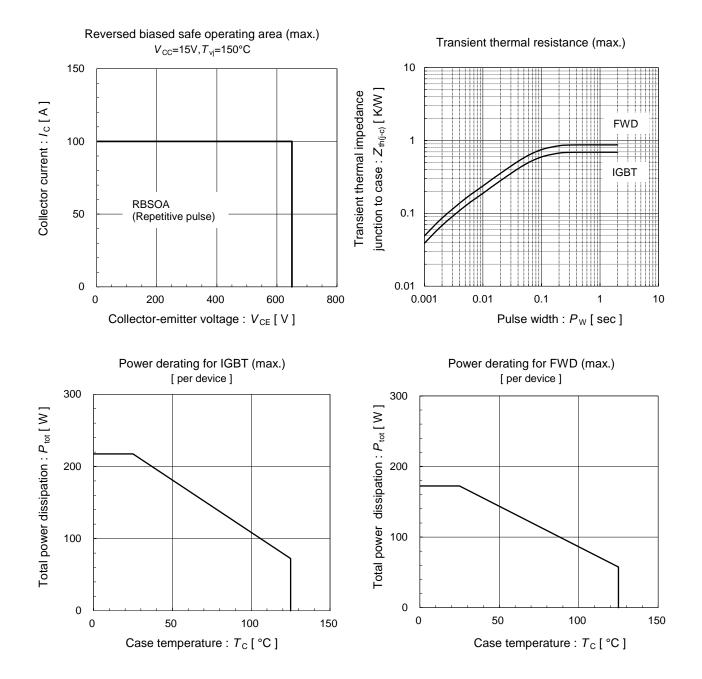
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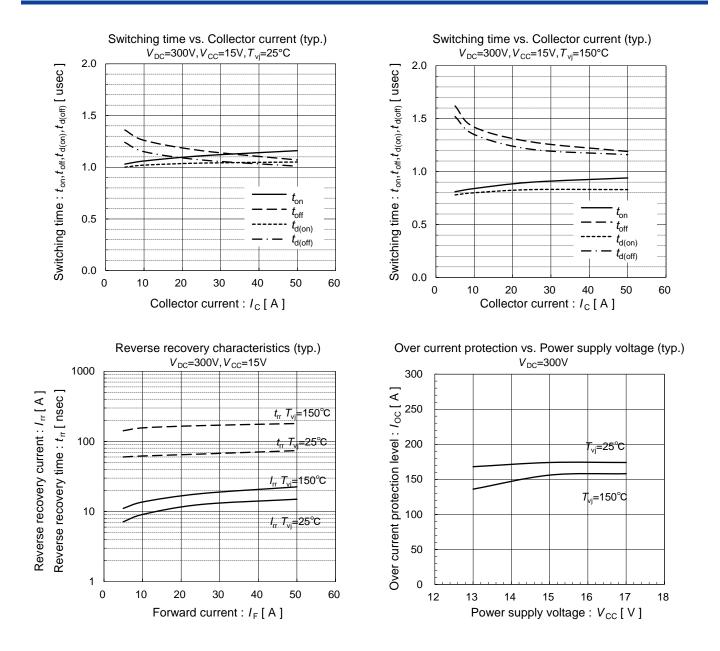








For Fuji Electric 6MBP50XBA065-50





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